

P27157.A03



Serial No.: 10/689,506

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of:

Docket No. P27157

Haujie CHEN, *et al.*

Confirmation No. 4303

Appln. No. : 10/689,506

Group Art Unit: 2813

Filed : October 20, 2003

Examiner: N. O. Berezny

For : HIGH PERFORMANCE STRESS-ENHANCED MOSFETs USING Si:C
AND SiGe EPITAXIAL SOURCE/DRAIN AND METHOD OF
MANUFACTURE

Commissioner for Patents
U.S. Patent and Trademark Office
Customer Service Window, Mail Stop Amendment
Randolph Building
401 Dulany Street
Alexandria VA 22314

SUPPLEMENTAL REQUEST FOR RECONSIDERATION

UNDER 37 C.F.R. §1.111

Sir:

In response to the Office Action dated May 17, 2005, Applicants request reconsideration of the rejected claims in view of the following remarks.

If extensions of time are necessary to prevent abandonment of this application, then such extensions of time are hereby petitioned under 37 C.F.R. § 1.136(a), and any fees required therefore (including fees for net addition of claims) are hereby authorized to be charged to Deposit Account No. 09-0458.

Amendments to the claims begin on page 2; and

Remarks begin on page 6.